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FDC6312P

Dual P-Channel 1.8V PowerTrench® Specified MOSFET

General Description

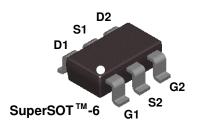
These P-Channel 1.8V specified MOSFETs are produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize on-state resistance and yet maintain low gate charge for superior switching performance.

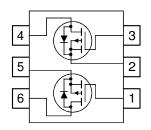
Applications

- Power management
- Load switch

Features

- $\begin{array}{c} \bullet \ \ -2.3 \ A, \, -20 \ V. \ \ R_{DS(ON)} = 115 \ m\Omega \ @ \ V_{GS} = -4.5 \ V \\ R_{DS(ON)} = 155 \ m\Omega \ @ \ V_{GS} = -2.5 \ V \\ R_{DS(ON)} = 225 \ m\Omega \ @ \ V_{GS} = -1.8 \ V \end{array}$
- High performance trench technology for extremely low $\mathbf{R}_{\scriptscriptstyle{\mathrm{DS(ON)}}}$
- SuperSOTTM-6 package: small footprint (72% smaller than standard SO-8); low profile (1mm thick)





Absolute Maximum Ratings TA=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-Source Voltage		-20	V
V _{GSS}	Gate-Source Voltage		±8	V
I _D	Drain Current - Continuous	(Note 1a)	-2.3	Α
	– Pulsed		– 7	
P _D	Power Dissipation for Single Operation	(Note 1a)	0.96	W
		(Note 1b)	0.9	
		(Note 1c)	0.7	
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	130	°C/W
$R_{ heta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	60	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
.312	FDC6312P	13"	12mm	3000 units

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics	1	I		I	I
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	-20			V
ΔBV _{DSS} ΔT _J	Breakdown Voltage Temperature Coefficient	$I_D = -250 \mu A$, Referenced to $25^{\circ}C$		-11		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μА
I _{GSSF}	Gate-Body Leakage, Forward	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{GS} = 8 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA
I _{GSSR}	Gate-Body Leakage, Reverse	$V_{GS} = -8 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-0.4	-0.9	-1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250 \mu\text{A}$, Referenced to 25°C		2		mV/°C
$R_{DS(on)}$	Static Drain–Source On–Resistance	$\begin{split} V_{GS} = -4.5 \ V, & I_D = -2.3 \ A \\ V_{GS} = -2.5 \ V, & I_D = -1.9 \ A \\ V_{GS} = -1.8 \ V, & I_D = -1.6 \ A \\ V_{GS} = -4.5 \ V, I_D = -2.3 A, T_J = 125 ^{\circ} C \end{split}$		92 116 166 112	115 155 225 150	mΩ
I _{D(on)}	On-State Drain Current	$V_{GS} = -4.5 \text{ V}, \qquad V_{DS} = -5 \text{ V}$	-7			Α
g _{FS}	Forward Transconductance	$V_{DS} = -5 \text{ V}, \qquad I_{D} = -3.5 \text{ A}$		5.3		S
Dynamic	Characteristics					
Ciss	Input Capacitance	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V},$		467		pF
Coss	Output Capacitance	f = 1.0 MHz		85	ĺ	pF
C _{rss}	Reverse Transfer Capacitance			38		pF
Switchir	g Characteristics (Note 2)					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = -10 \text{ V}, \qquad I_{D} = -1 \text{ A},$		8	16	ns
t _r	Turn-On Rise Time	$V_{GS} = -4.5 \text{ V}, \qquad R_{GEN} = 6 \Omega$		13	23	ns
t _{d(off)}	Turn-Off Delay Time	1		18	32	ns
t _f	Turn-Off Fall Time	1		8	16	ns
Qg	Total Gate Charge	$V_{DS} = -10 \text{ V}, \qquad I_{D} = -2.3 \text{ A},$		4.4	7	nC
Q _{gs}	Gate-Source Charge	$V_{GS} = -4.5 \text{ V}$		1.0		nC
Q_{gd}	Gate-Drain Charge	_		0.8		nC
	ource Diode Characteristics	and Maximum Ratings	•		•	
l _s	Maximum Continuous Drain–Source				-0.8	Α
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = -0.8 \text{ A} \text{(Note 2)}$		-0.7	-1.2	V

Notes

^{1.} R_{BJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{BJC} is guaranteed by design while R_{BCA} is determined by the user's board design.



 a) 130 °C/W when mounted on a 0.125 in² pad of 2 oz. copper.



b) 140°/W when mounted on a .004 in² pad of 2 oz copper

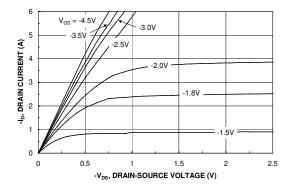


c) 180°/W when mounted on a minimum pad.

Scale 1:1 on letter size paper

2. Pulse Test: Pulse Width < 300µs, Duty Cycle < 2.0%

Typical Characteristics



2.5

OBANALIZED

OBANALIZED

1.75

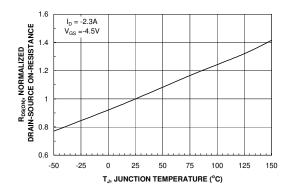
O 1 2 3 4 5 60

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OBA

Figure 1. On-Region Characteristics.

Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.



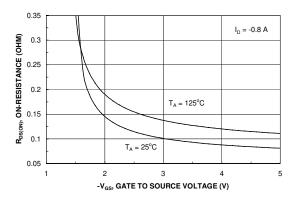
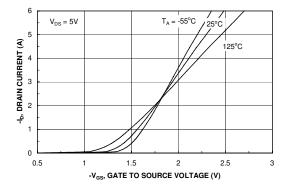


Figure 3. On-Resistance Variation with Temperature.

Figure 4. On-Resistance Variation with Gate-to-Source Voltage.



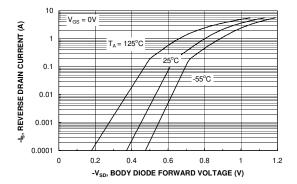
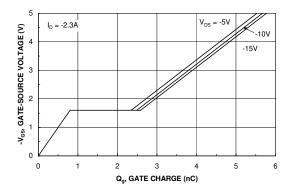


Figure 5. Transfer Characteristics.

Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics



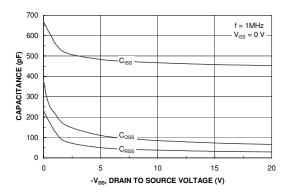


Figure 7. Gate Charge Characteristics.

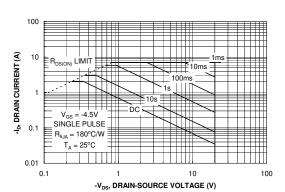


Figure 8. Capacitance Characteristics.

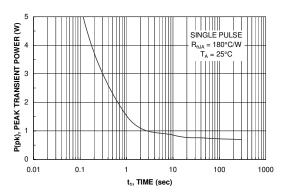


Figure 9. Maximum Safe Operating Area.



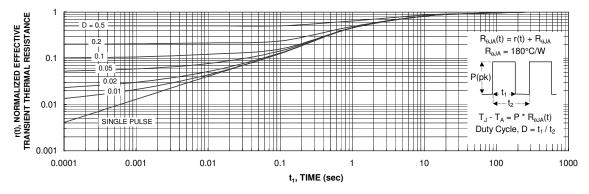


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.

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